High Current Transistors

NPN Silicon

Features

• These are Pb-Free Devices*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	80	Vdc
Collector - Base Voltage	V _{CBO}	80	Vdc
Collector - Emitter Voltage	V _{EBO}	5.0	Vdc
Collector Current – Continuous	Ic	0.5	Adc
Total Power Dissipation @ T _A = 25°C Derate above T _A = 25°C	P _D	625 5.0	mW mW/°C
Total Power Dissipation @ T _A = 25°C Derate above T _A = 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

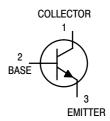
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

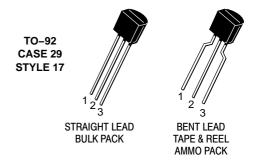
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



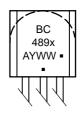
ON Semiconductor®

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MARKING DIAGRAM



489x = 489A

A = Assembly Location

Y = Year WW = Work Week Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BC489G	TO-92 (Pb-Free)	5000 Units / Bulk
BC489RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC489AG	TO-92 (Pb-Free)	5000 Units / Bulk

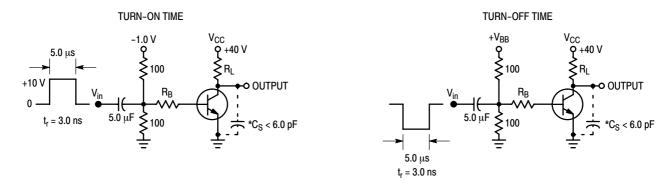
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

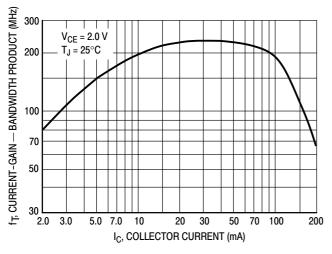
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	<u> </u>	<u>I</u>		<u> </u>	
Collector – Emitter Breakdown Voltage (Note 1) (I _C = 10 mAdc, I _B = 0)	V _{(BR)CEO}	80	_	_	Vdc
Collector – Base Breakdown Voltage ($I_C = 100 \mu Adc$, $I_E = 0$)	V _{(BR)CBO}	80	-	-	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)	V _{(BR)EBO}	5.0	-	_	Vdc
Collector Cutoff Current (V _{CB} = 60 V, I _E = 0)	I _{CBO}	_	-	100	nAdc
ON CHARACTERISTICS					
DC Current Gain $ \begin{aligned} &(I_C=10 \text{ mAdc, V}_{CE}=2.0 \text{ Vdc}) \\ &(I_C=100 \text{ mAdc, V}_{CE}=2.0 \text{ Vdc}) \end{aligned} \qquad \qquad \text{BC489} \\ &\text{BC489A} $	h _{FE}	40 60 100	- - 160	- 400 250	_
$(I_C = 1.0 \text{ Adc}, V_{CE} = 5.0 \text{ Vdc})$		15	-	_	
Collector – Emitter Saturation Voltage ($I_C = 500 \text{ mAdc}$, $I_B = 50 \text{ mAdc}$) ($I_C = 1.0 \text{ Adc}$, $I_B = 100 \text{ mAdc}$)	V _{CE(sat)}	- -	0.2 0.3	0.5 -	Vdc
Collector – Emitter Saturation Voltage ($I_C = 500 \text{ mAdc}$, $I_B = 50 \text{ mAdc}$) ($I_C = 1.0 \text{ Adc}$, $I_B = 100 \text{ mAdc}$) (Note 1)	V _{BE(sat)}	- -	0.85 0.9	1.2	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain – Bandwidth Product (I _C = 50 mAdc, V _{CE} = 2.0 Vdc, f = 100 MHz)	f _T	-	200	-	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)	C _{ob}	-	7.0	-	pF
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}$, $I_{C} = 0$, $f = 1.0 \text{ MHz}$)	C _{ib}	-	50	-	pF

^{1.} Pulse Test: Pulse Width = 300 μs, Duty Cycle 2.0%.



^{*}Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits



80 60 40 C, CAPACITANCE (pF) 20 10 8.0 6.0 4.0 0.2 0.1 0.5 1.0 2.0 5.0 50 100 V_R, REVERSE VOLTAGE (VOLTS)

Figure 2. Current-Gain — Bandwidth Product

Figure 3. Capacitance

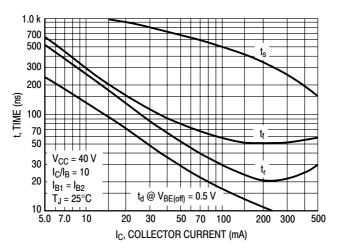


Figure 4. Switching Time

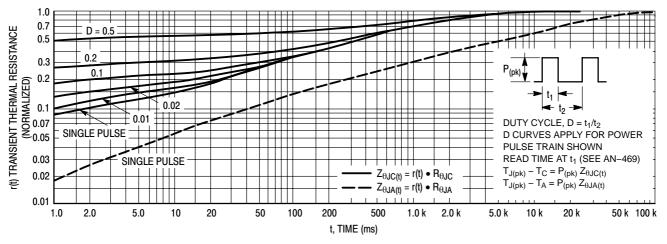


Figure 5. Thermal Response

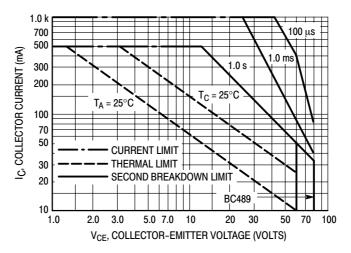


Figure 6. Active Region — Safe Operating Area

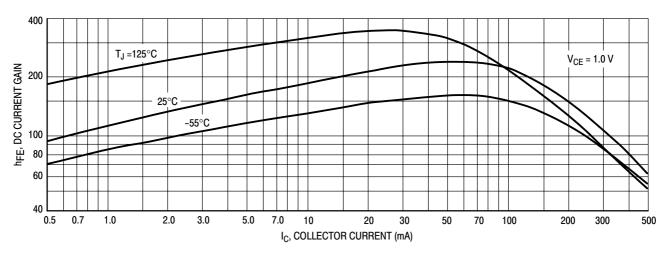


Figure 7. DC Current Gain

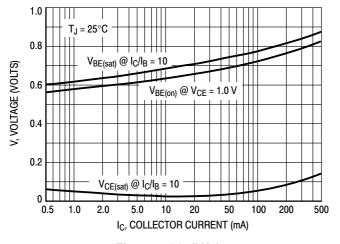


Figure 8. "On" Voltages

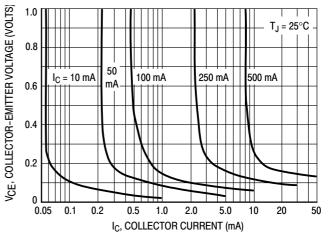


Figure 9. Collector Saturation Region

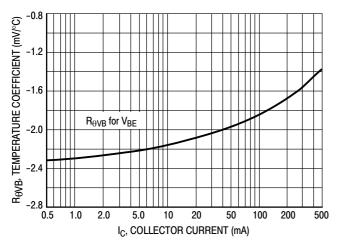


Figure 10. Base-Emitter Temperature Coefficient

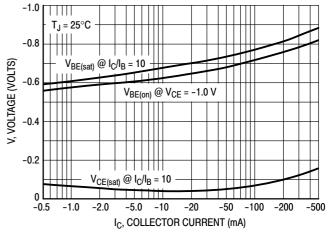


Figure 11. "On" Voltages

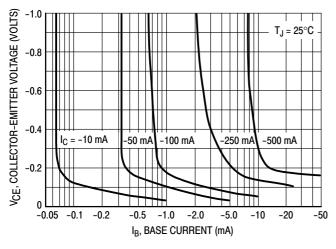


Figure 12. Collector Saturation Region

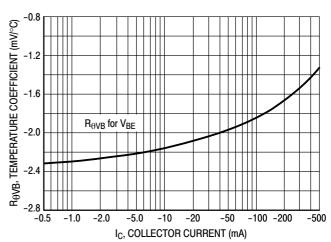
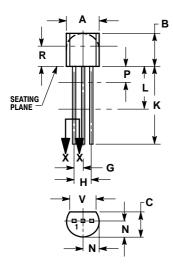


Figure 13. Base-Emitter Temperature Coefficient

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**



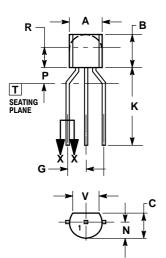
STRAIGHT LEAD **BULK PACK**



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3 43	



BENT LEAD TAPE & REEL AMMO PACK



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
 CONTOUR OF PACKAGE BEYOND
- DIMENSION R IS UNCONTROLLED
- LEAD DIMENSION IS UNCONTROLLED IN PAND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN MAX		
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
Р	1.50	4.00	
R	2.93		
٧	3.43		

STYLE 17:

COLLECTOR PIN 1.

BASE

EMITTER

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